

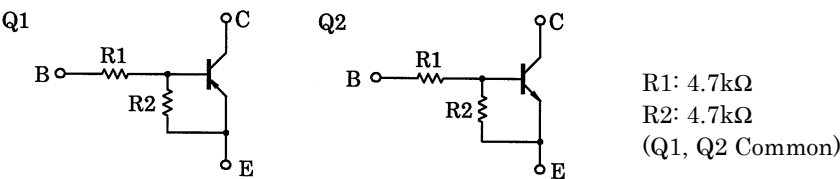
TOSHIBA Transistor  
Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

RN4601

Switching, Inverter Circuit, Interface Circuit  
And Driver Circuit Applications

- Includeing two devices in SM6 (super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit and Bias Resister Values

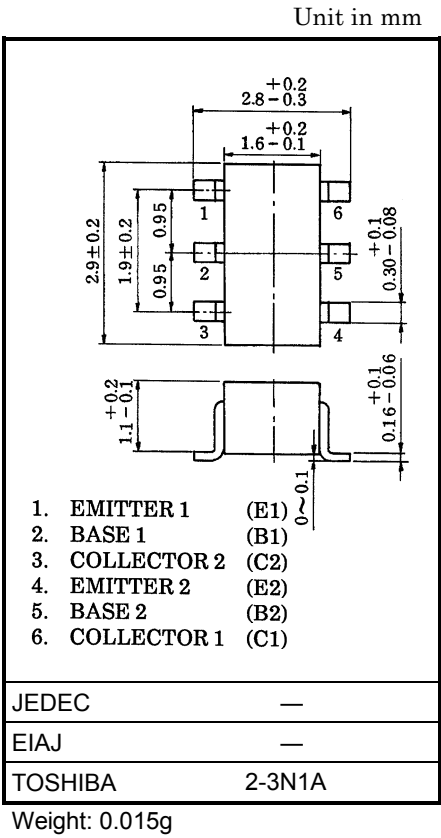


Q1 Maximum Ratings (Ta = 25°C)

| Characteristic            | Symbol           | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-base voltage    | V <sub>CBO</sub> | -50    | V    |
| Collector-emitter voltage | V <sub>CEO</sub> | -50    | V    |
| Emitter-base voltage      | V <sub>EBO</sub> | -10    | V    |
| Collector current         | I <sub>C</sub>   | -100   | mA   |

Q2 Maximum Ratings (Ta = 25°C)

| Characteristic            | Symbol           | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-base voltage    | V <sub>CBO</sub> | 50     | V    |
| Collector-emitter voltage | V <sub>CEO</sub> | 50     | V    |
| Emitter-base voltage      | V <sub>EBO</sub> | 10     | V    |
| Collector current         | I <sub>C</sub>   | 100    | mA   |

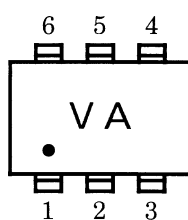


## Q1, Q2 Common Maximum Ratings (Ta = 25°C)

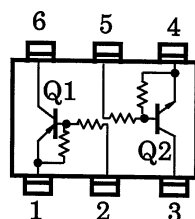
| Characteristic              | Symbol    | Rating  | Unit |
|-----------------------------|-----------|---------|------|
| Collector power dissipation | $P_C^*$   | 300     | mW   |
| Junction temperature        | $T_j$     | 150     | °C   |
| Storage temperature range   | $T_{stg}$ | -55~150 | °C   |

\* : Total rating

## Marking



## Equivalent Circuit (Top View)



**Q1 Electrical Characteristics (Ta = 25°C)**

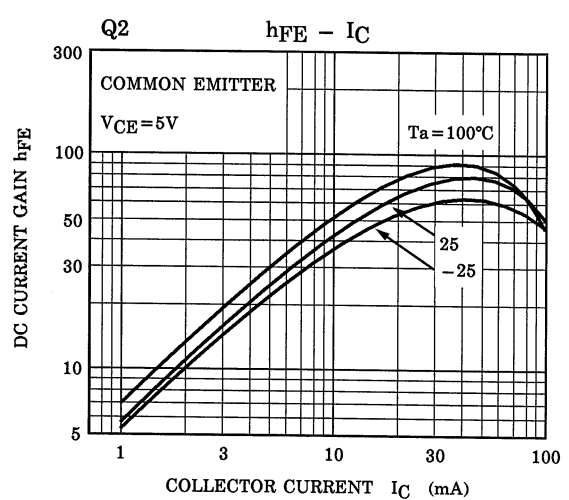
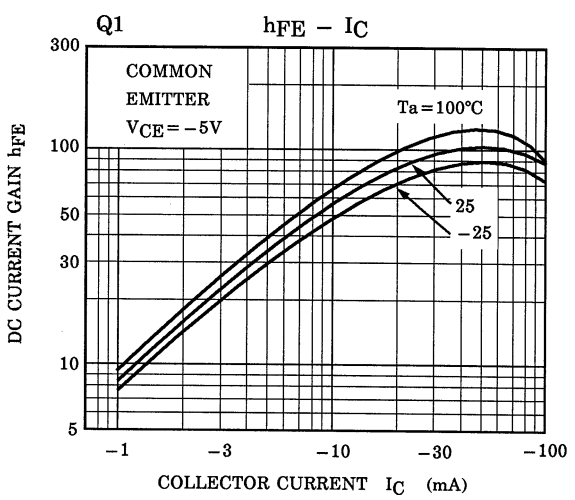
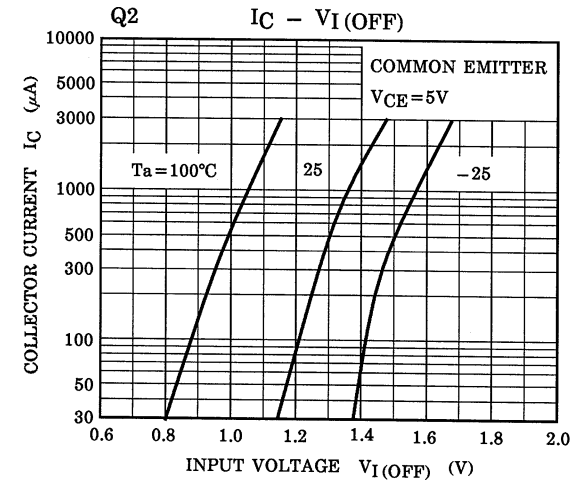
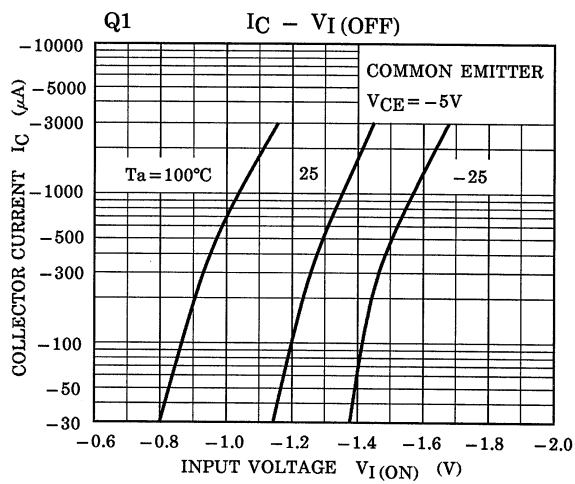
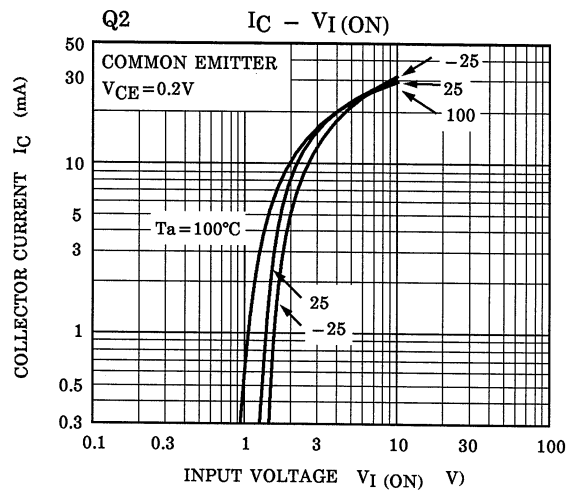
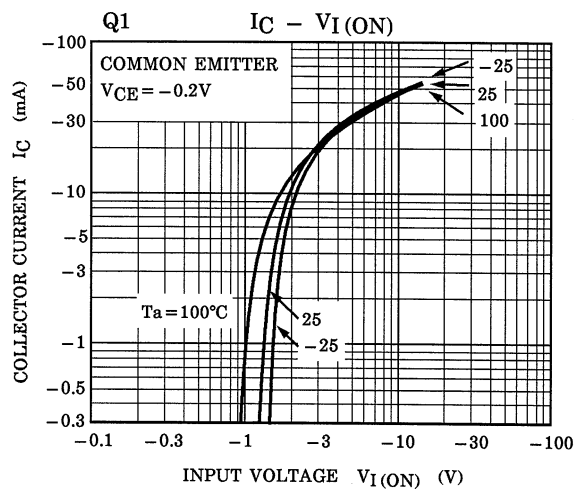
| Characteristic                       | Symbol                | Test Circuit | Test Condition                                       | Min   | Typ. | Max   | Unit |
|--------------------------------------|-----------------------|--------------|--|-------|------|-------|------|
| Collector cut-off current            | I <sub>CBO</sub>      | —            | V <sub>CB</sub> = -50V, I <sub>E</sub> = 0           | —     | —    | -100  | nA   |
|                                      | I <sub>CEO</sub>      | —            | V <sub>CE</sub> = -50V, I <sub>B</sub> = 0           | —     | —    | -500  |      |
| Emitter cut-off current              | I <sub>EBO</sub>      | —            | V <sub>EB</sub> = -10V, I <sub>C</sub> = 0           | -0.82 | —    | -1.52 | mA   |
| DC current gain                      | h <sub>FE</sub>       | —            | V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA        | 30    | —    | —     | —    |
| Collector-emitter saturation voltage | V <sub>CE (sat)</sub> | —            | I <sub>C</sub> = -5mA, I <sub>B</sub> = -0.25mA      | —     | -0.1 | -0.3  | V    |
| Input voltage (ON)                   | V <sub>I (ON)</sub>   | —            | V <sub>CE</sub> = -0.2V, I <sub>C</sub> = -5mA       | -1.1  | —    | -2.0  | V    |
| Input voltage (OFF)                  | V <sub>I (OFF)</sub>  | —            | V <sub>CE</sub> = -5V, I <sub>C</sub> = -0.1mA       | -1.0  | —    | -1.5  | V    |
| Transition frequency                 | f <sub>T</sub>        | —            | V <sub>CE</sub> = -10V, I <sub>C</sub> = -5mA        | —     | 200  | —     | MHz  |
| Collector output capacitance         | C <sub>ob</sub>       | —            | V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz | —     | 3    | 6     | pF   |

**Q2 Electrical Characteristics (Ta = 25°C)**

| Characteristic                       | Symbol                | Test Circuit | Test Condition                                       | Min  | Typ. | Max  | Unit |
|--------------------------------------|-----------------------|--------------|--|------|------|------|------|
| Collector cut-off current            | I <sub>CBO</sub>      | —            | V <sub>CB</sub> = 50V, I <sub>E</sub> = 0            | —    | —    | 100  | nA   |
|                                      | I <sub>CEO</sub>      | —            | V <sub>CE</sub> = 50V, I <sub>B</sub> = 0            | —    | —    | 500  |      |
| Emitter cut-off current              | I <sub>EBO</sub>      | —            | V <sub>EB</sub> = 10V, I <sub>C</sub> = 0            | 0.82 | —    | 1.52 | mA   |
| DC current gain                      | h <sub>FE</sub>       | —            | V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA          | 30   | —    | —    | —    |
| Collector-emitter saturation voltage | V <sub>CE (sat)</sub> | —            | I <sub>C</sub> = 5mA, I <sub>B</sub> = 0.25mA        | —    | 0.1  | 0.3  | V    |
| Input voltage (ON)                   | V <sub>I (ON)</sub>   | —            | V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 5mA         | 1.1  | —    | 2.0  | V    |
| Input voltage (OFF)                  | V <sub>I (OFF)</sub>  | —            | V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.1mA         | 1.0  | —    | 1.5  | V    |
| Transition frequency                 | f <sub>T</sub>        | —            | V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA          | —    | 250  | —    | MHz  |
| Collector output capacitance         | C <sub>ob</sub>       | —            | V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1 MHz | —    | 3    | 6    | pF   |

**Q1, Q2 Common Electrical Characteristics (Ta = 25°C)**

| Characteristic | Symbol | Test Circuit | Test Condition | Min  | Typ. | Max  | Unit |
|----------------|--------|--------------|----------------|------|------|------|------|
| Input resistor | R1     | —            | —              | 3.29 | 4.7  | 6.11 | kΩ   |
| Resistor ratio | R1/R2  | —            | —              | 0.9  | 1.0  | 1.1  | —    |



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